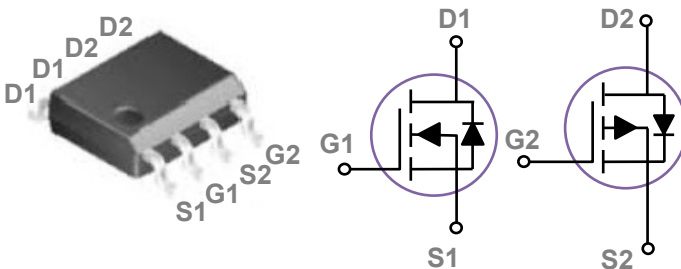


### General Description

These N+P dual Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
30V	13mΩ	10A
-30V	30mΩ	-6.5A

### SOP8 Pin Configuration



### Features

- Fast switching
- Green Device Available
- Suit for 4.5V Gate Drive Applications

### Applications

- DC Fan
- Motor Drive Applications
- Networking
- Half / Full Bridge Topology

### Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating		Units
$V_{DS}$	Drain-Source Voltage	30	-30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	$\pm 20$	V
$I_D$	Drain Current – Continuous ( $T_c=25^\circ\text{C}$ )	10	-6.5	A
	Drain Current – Continuous ( $T_c=100^\circ\text{C}$ )	6.3	-4.1	A
$I_{DM}$	Drain Current – Pulsed <sup>1</sup>	36	-26	A
$P_D$	Power Dissipation ( $T_c=25^\circ\text{C}$ )	5		W
	Power Dissipation – Derate above $25^\circ\text{C}$	0.04		W/ $^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150		$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150		$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62.5	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	25	$^\circ\text{C}/\text{W}$

**N-CH Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise)**
**Off Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=30V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	$\mu A$
		$V_{DS}=24V, V_{GS}=0V, T_J=125^\circ\text{C}$	---	---	10	$\mu A$
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA

**On Characteristics**

$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=8A$	---	10	13	$m\Omega$
		$V_{GS}=4.5V, I_D=4A$	---	14	18	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.6	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4	---	$mV/^\circ\text{C}$
$g_{fs}$	Forward Transconductance	$V_{DS}=10V, I_D=3A$	---	6	---	S

**Dynamic and switching Characteristics**

$Q_g$	Total Gate Charge <sup>3,4</sup>	$V_{DS}=15V, V_{GS}=4.5V, I_D=5A$	---	7.4	12	nC
$Q_{gs}$	Gate-Source Charge <sup>3,4</sup>		---	2.3	5	
$Q_{gd}$	Gate-Drain Charge <sup>3,4</sup>		---	3	6	
$T_{d(on)}$	Turn-On Delay Time <sup>3,4</sup>	$V_{DD}=15V, V_{GS}=10V, R_G=6\Omega$ $I_D=1A$	---	3.8	7	ns
$T_r$	Rise Time <sup>3,4</sup>		---	10	19	
$T_{d(off)}$	Turn-Off Delay Time <sup>3,4</sup>		---	22	42	
$T_f$	Fall Time <sup>3,4</sup>		---	6.6	13	
$C_{iss}$	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, F=1\text{MHz}$	---	620	900	pF
$C_{oss}$	Output Capacitance		---	85	125	
$C_{rss}$	Reverse Transfer Capacitance		---	60	90	
$R_g$	Gate resistance	$V_{GS}=0V, V_{DS}=0V, f=1\text{MHz}$	---	2.8	5.6	$\Omega$

**Drain-Source Diode Characteristics and Maximum Ratings**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current	$V_G=V_D=0V$ , Force Current	---	---	10	A
$I_{SM}$	Pulsed Source Current		---	---	20	A
$V_{SD}$	Diode Forward Voltage	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$ .
3. Essentially independent of operating temperature.

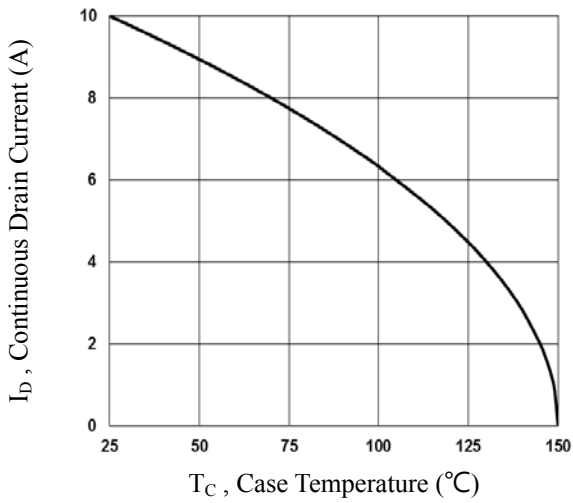


Fig.1 Continuous Drain Current vs.  $T_c$

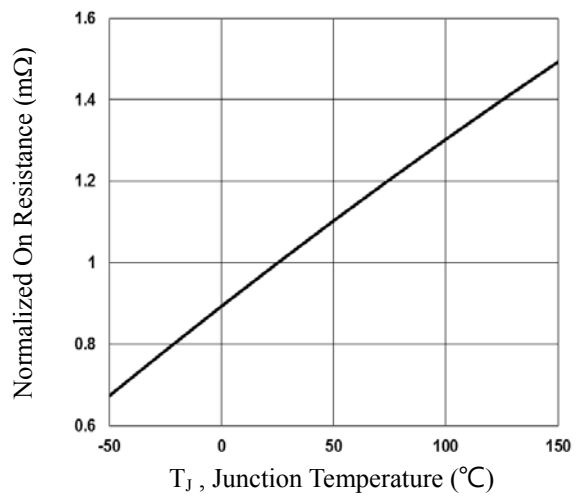


Fig.2 Normalized  $R_{DS(on)}$  vs.  $T_j$

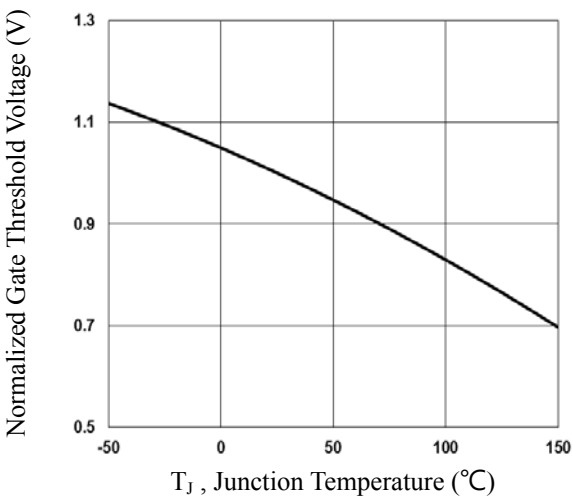


Fig.3 Normalized  $V_{th}$  vs.  $T_j$

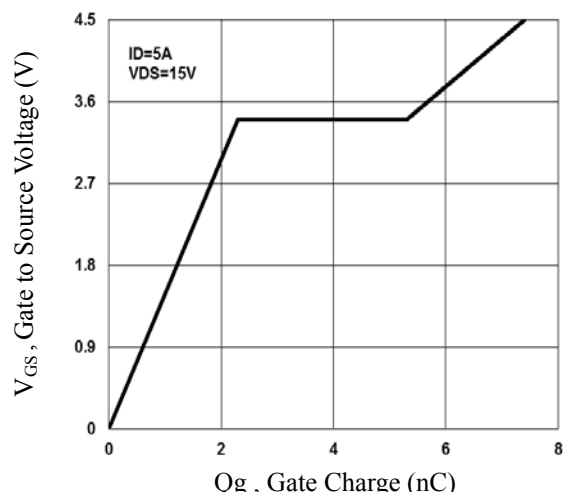


Fig.4 Gate Charge Waveform

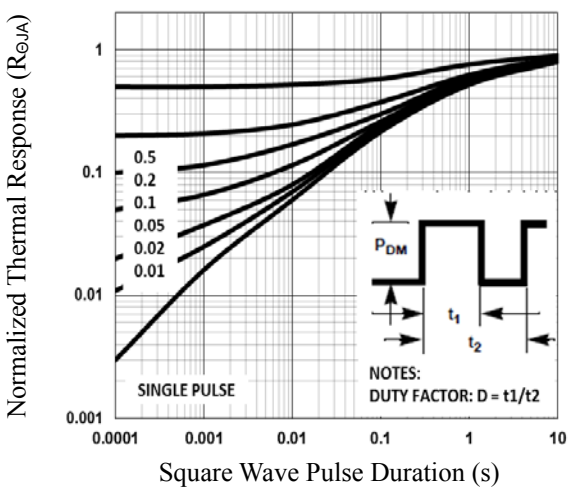


Fig.5 Normalized Transient Response

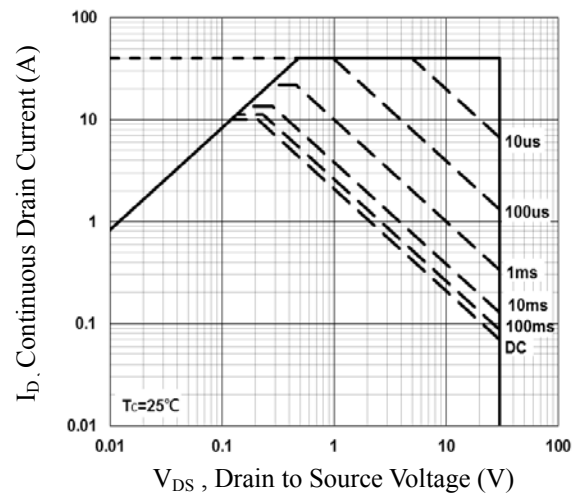


Fig.6 Maximum Safe Operation Area

**P-CH Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise**
**Off Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-30	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =-1mA	---	-0.03	---	V/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	-1	uA
		V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C	---	---	-10	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA

**On Characteristics**

R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-10V, I <sub>D</sub> =-6A	---	24	30	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4A	---	37	46	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-1	-1.6	-2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	4	---	mV/°C
gfs	Forward Transconductance	V <sub>DS</sub> =-10V, I <sub>D</sub> =-3A	---	9	---	S

**Dynamic and switching Characteristics**

Q <sub>g</sub>	Total Gate Charge <sup>2,3</sup>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-5A	---	8	15	nC
Q <sub>gs</sub>	Gate-Source Charge <sup>2,3</sup>		---	3.3	6	
Q <sub>gd</sub>	Gate-Drain Charge <sup>2,3</sup>		---	2.3	5	
T <sub>d(on)</sub>	Turn-On Delay Time <sup>2,3</sup>	V <sub>DD</sub> =-15V, V <sub>GS</sub> =-10V, R <sub>G</sub> =6Ω	---	4.6	9	ns
T <sub>r</sub>	Rise Time <sup>2,3</sup>		---	14	26	
T <sub>d(off)</sub>	Turn-Off Delay Time <sup>2,3</sup>		I <sub>D</sub> =-1A	---	34	
T <sub>f</sub>	Fall Time <sup>2,3</sup>		---	18	35	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, F=1MHz	---	757	1280	pF
C <sub>oss</sub>	Output Capacitance		---	122	210	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	88	175	

**Drain-Source Diode Characteristics and Maximum Ratings**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	-6.5	A
I <sub>SM</sub>	Pulsed Source Current		---	---	-13	A
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =-1A, T <sub>J</sub> =25°C	---	---	-1	V

Note :

4. Repetitive Rating : Pulsed width limited by maximum junction temperature.
5. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
6. Essentially independent of operating temperature.

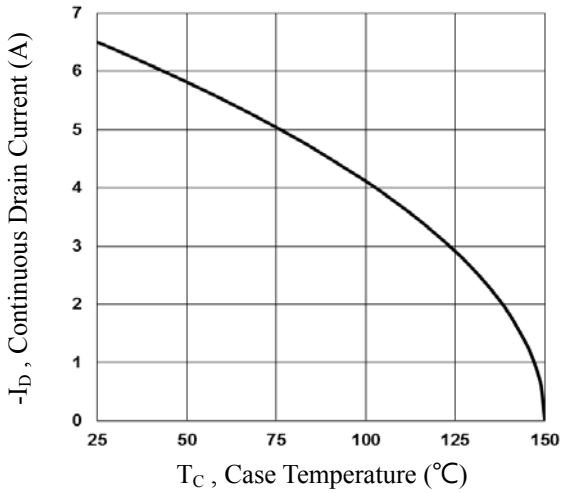


Fig.1 Continuous Drain Current vs.  $T_c$

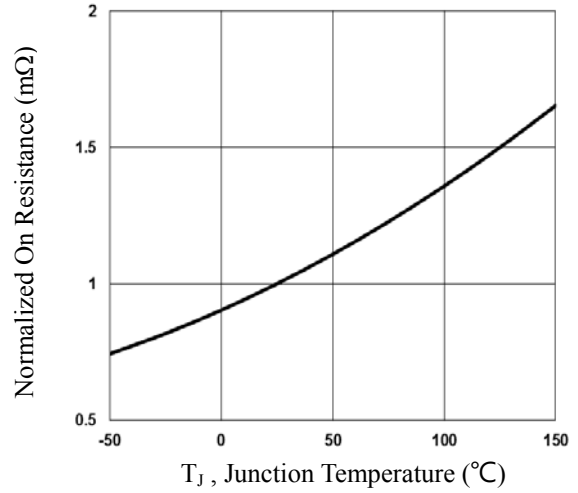


Fig.2 Normalized  $R_{DS(on)}$  vs.  $T_j$

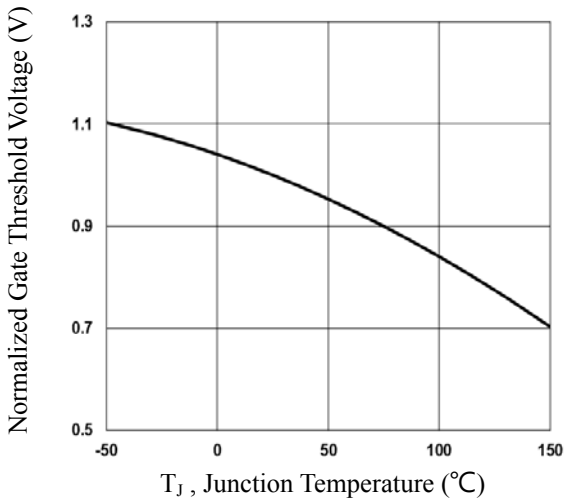


Fig.3 Normalized  $V_{th}$  vs.  $T_j$

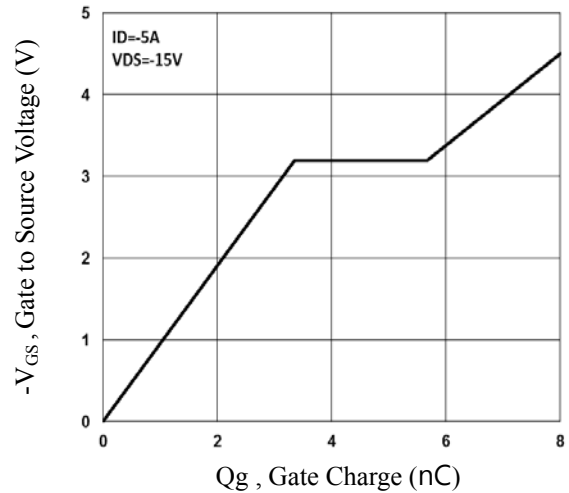


Fig.4 Gate Charge Waveform

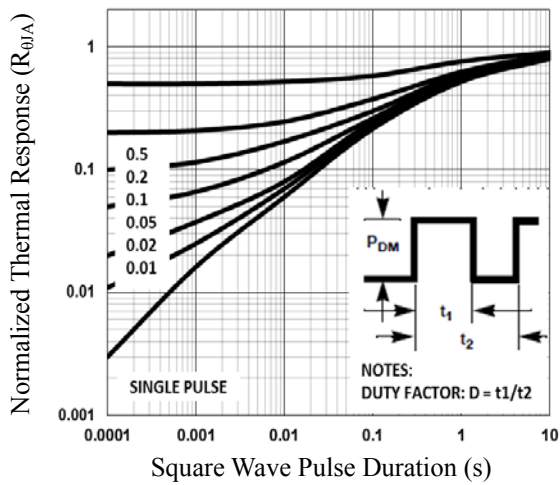


Fig.5 Normalized Transient Impedance

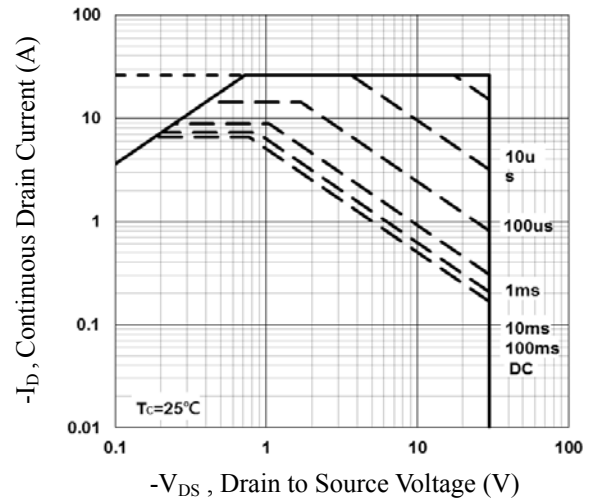
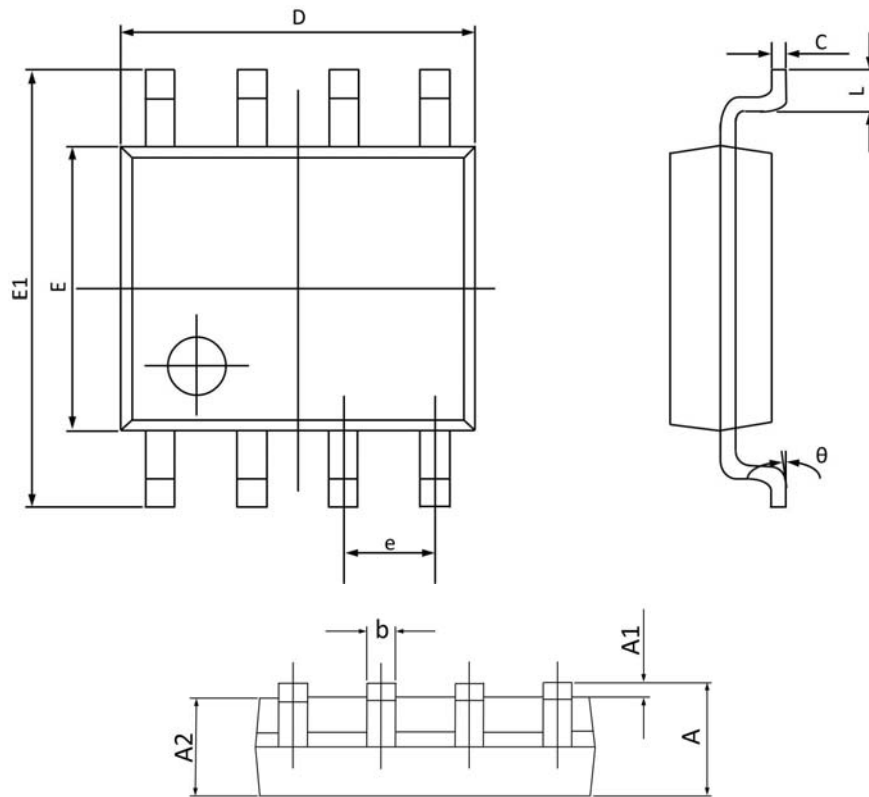


Fig.6 Maximum Safe Operation Area

## SOP8 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	1.750	1.350	0.069	0.053
A1	0.250	0.100	0.010	0.004
A2	1.500	1.300	0.059	0.051
b	0.490	0.350	0.019	0.014
C	0.260	0.190	0.010	0.007
D	5.100	4.700	0.201	0.185
E	4.100	3.700	0.161	0.146
E1	6.200	5.800	0.244	0.228
e	1.27BSC		0.05BSC	
L	0.900	0.400	0.035	0.016
$\theta$	8°	0°	8°	0°